ABSTRACT

An object of the present invention is to provide a flip-chip-type gallium nitride compound semiconductor light-emitting device exhibiting excellent ohmic characteristics, excellent bonding characteristics, and high emission output.

The inventive flip-chip-type gallium nitride compound semiconductor light-emitting device comprises a substrate, an n-type semiconductor layer, a light-emitting layer, a p-type semiconductor layer, a negative electrode provided on the n-type semiconductor layer, and a positive electrode provided on the p-type semiconductor layer, the layers being successively provided atop the substrate in this order and being composed of a gallium nitride compound semiconductor, wherein the positive electrode has a three-layer structure comprising an ohmic electrode layer which is in contact with the p-type semiconductor layer, an adhesion layer which is provided on the ohmic electrode layer, and a bonding pad layer provided on the adhesion layer, each melting point of these layers being lowered in this order.